





#### 120V NPN MEDIUM POWER DARLINGTON TRANSISTOR IN POWERDI®5

#### **Features**

- BV<sub>CEO</sub> > 120V
- BV<sub>CBO</sub> > 140V
- I<sub>C</sub> = 1.5A High Continuous current
- hFE > 2k for High Gain @ 1A
- 43% smaller than SOT223; 60% smaller than TO252
- Maximum Height Just 1.1mm
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: POWERDI5
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.093 grams (approximate)

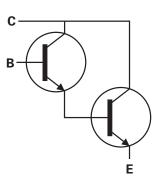
#### **Applications**

- DC Fans
- Regulator Transistors
- Relays
- Solenoid Driving

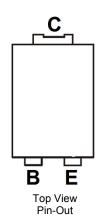








**Equivalent Circuit** 



#### Ordering Information (Note 4)

Product	Package	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN04120HP5TC	POWERDI5	ZXTN04120H	13	16	5,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



ZXTN04120H = Product Type Marking Code K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 13 for 2013) WW = Week code (01 to 53)





### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	140	V
Collector-Emitter Voltage	$V_{CEO}$	120	V
Emitter-Base Voltage	$V_{EBO}$	14	V
Continuous Collector Current	Ic	1.5	Α
Peak Pulse Current	Ісм	4	Α

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.2		
Power Dissipation	(Note 6)	$P_{D}$	1.7	W	
	(Note 7)		0.74		
	(Note 5)		39		
Thermal Resistance, Junction to Ambient Air	(Note 6)	R <sub>0JA</sub>	75		
	(Note 7)		169	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	9		
Thermal Resistance, Junction to Case	(Note 9)	$R_{ heta JC}$	10		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

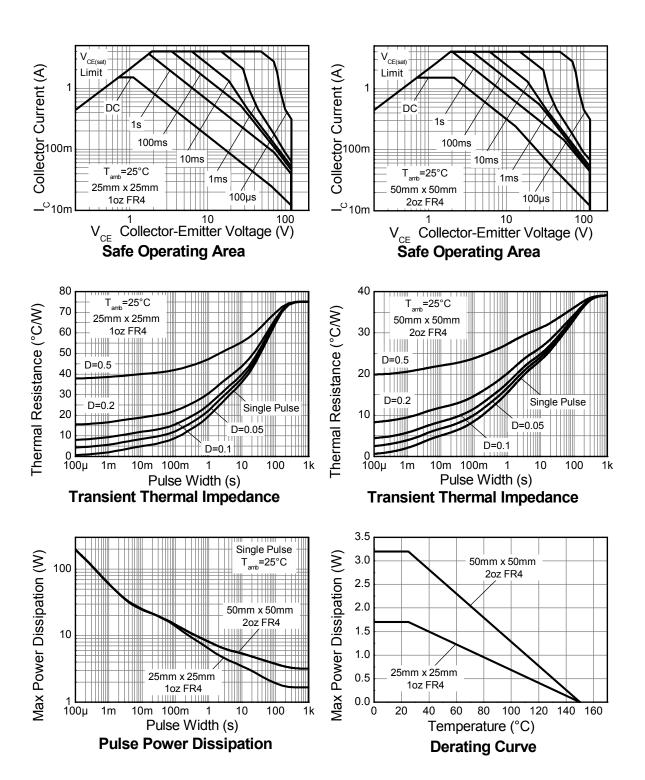
Notes:

- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- Same as note (5), except mounted on 25mm x 25mm 1oz copper.
- Same as note (5), except mounted on minimum recommended pad (MRP) layout.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
- Thermal resistance from junction to the top of the case.
  Refer to JEDEC specification JESD22-A114 and JESD22-A115.





## **Thermal Characteristics and Derating Information**







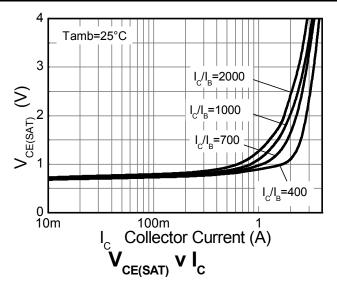
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

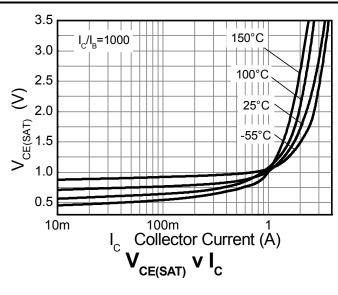
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	140	_	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	120	_	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	14	_	_	V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	100 10	nΑ μΑ	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +120°C
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	_	100	nA	V <sub>CE</sub> = 120V
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 8V
DC Current Gain (Note 11)	h <sub>FE</sub>	2,000 5,000 2,000 500	_ _ _ _	  100,000 	_	$I_{C} = 50$ mA, $V_{CE} = 5$ V $I_{C} = 500$ mA, $V_{CE} = 5$ V $I_{C} = 1$ A, $V_{CE} = 5$ V $I_{C} = 2$ A, $V_{CE} = 5$ V
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_	_	1 1.5	V	$I_C = 250$ mA, $I_B = 0.25$ mA $I_C = 1$ A, $I_B = 1$ mA
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	_	1.8	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 1mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	_	1.7	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 5V
Input Capacitance (Note 11)	C <sub>ibo</sub>	_	90	_	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance (Note 11)	Cobo	_	15	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 11)	f <sub>T</sub>	150	_	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f=20MHz
Turn-On Time	t <sub>on</sub>		0.5		μs	V <sub>CC</sub> = 10V, I <sub>C</sub> = 500mA
Turn-Off Time	t <sub>off</sub>	_	1.6	_	μs	$I_{B1} = -I_{B2} = 0.5 \text{mA}$

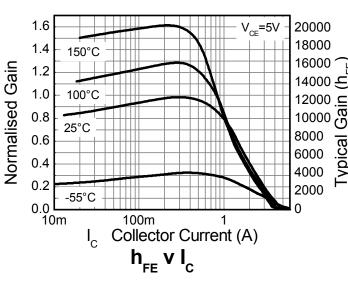
Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

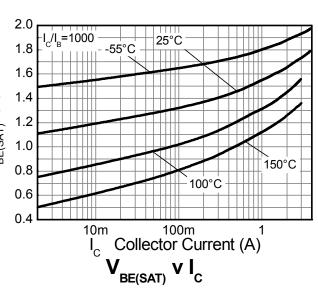


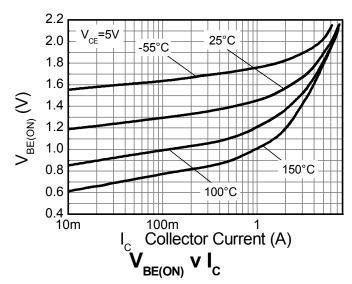
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)









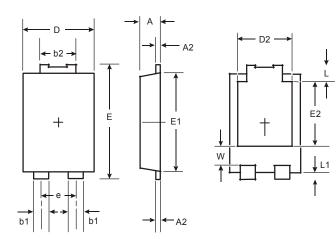






## **Package Outline Dimensions**

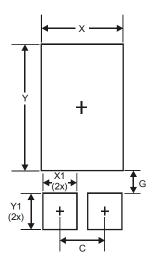
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI5					
Dim	Min	Max			
Α	1.05	1.15			
A2	0.33	0.43			
b1	0.80	0.99			
b2	1.70	1.88			
D	3.90	4.05			
D2	3.054 Typ				
Е	6.40	6.60			
е	1.84 Typ				
E1	5.30	5.45			
E2	3.549 Typ				
L	0.75	0.95			
L1	0.50	0.65			
W	1.10 1.41				
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
X	3.360
X1	1.390
Υ	4.860
Y1	1.400

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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